# 4V Drive Nch+Pch MOSFET **SP8M2**

#### ●Structure

Silicon N-channel MOSFET/ Silicon P-channel MOSFET

#### ● Features

- 1) Low on-resistance.
- 2) Built-in G-S protection diode.
- 3) Small surface mount package (SOP8).

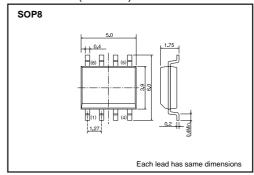
## Applications

Switching

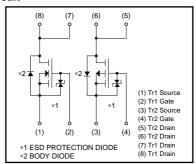
## Package specifications

	Package	Taping		
Type	Code	TB		
	Basic ordering unit (pieces)	2500		
SP8M2		0		

## ●Dimensions (Unit:mm)



#### ●Inner circuit



#### ● Absolute maximum ratings (Ta=25°C)

Parameter		Sumbol	Lin	Unit	
		Symbol	Tr1: N-ch Tr2: P-ch		Offic
Drain-source voltage		V <sub>DSS</sub>	30	-30	V
Gate-source voltage	Gate-source voltage		±20	±20	V
Drain current	Continuous	ID	±3.5	±3.5	Α
	Pulsed	I <sub>DP</sub> *1	±14	±14	А
Source current Continuo		Is	1.6 –1.6		Α
(Body diode)	Pulsed	Isp*1	14	-14	Α
Total power dissipation		P <sub>D</sub> *2	2.0		W / TOTAL
Channel temperature		Tch	150		°C
Storage temperature		Tstg	-55 to +150		°C

<sup>\*1</sup> Pw≤10μs, Duty cycle≤1%

N-ch

# ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	_	_	±10	μΑ	Vgs=±20V, Vps=0V
Drain-source breakdown voltage	V <sub>(BR)</sub> DSS	30	_	_	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	_	_	1	μΑ	V <sub>DS</sub> = 30V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	1.0	_	2.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Otatio Indiana and at a		_	59	83	mΩ	I <sub>D</sub> = 3.5A, V <sub>GS</sub> = 10V
Static drain-source on-state resistance	R <sub>DS (on)</sub> *	-	93	130	mΩ	I <sub>D</sub> = 3.5A, V <sub>GS</sub> = 4.5V
resistance		-	107	150	mΩ	I <sub>D</sub> = 3.5A, V <sub>GS</sub> = 4V
Forward transfer admittance	Y <sub>fs</sub>   *	2.0	-	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 3.5A
Input capacitance	Ciss	-	140	-	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	_	45	_	pF	Vgs=0V
Reverse transfer capacitance	Crss	_	30	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	_	6	_	ns	V <sub>DD</sub> ≒ 15V
Rise time	tr *	_	6	_	ns	ID= 1.75A
Turn-off delay time	t <sub>d (off)</sub> *	_	17	_	ns	V <sub>GS</sub> = 10V R <sub>L</sub> = 8.57Ω
Fall time	t <sub>f</sub> *	_	4	_	ns	R <sub>G</sub> =10Ω
Total gate charge	Qg *	_	2.5	3.5	nC	V <sub>DD</sub> ≒15V, V <sub>GS</sub> =5V
Gate-source charge	Q <sub>gs</sub> *	_	0.8	_	nC	I <sub>D</sub> = 3.5A
Gate-drain charge	Q <sub>gd</sub> *	_	0.8	_	nC	$R_L=4.29\Omega$ , $R_G=10\Omega$

<sup>\*</sup>Pulsed

# $\bullet \textbf{Body diode characteristics} \ (Source-drain) \ (Ta=25^{\circ}C)$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp*	-	_	1.2	V	I <sub>S</sub> = 6.4A, V <sub>GS</sub> =0V

<sup>\*</sup>Pulsed

P-ch

## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	_	±10	μΑ	Vgs= ±20V, Vps=0V
Drain-source breakdown voltage	V <sub>(BR) DSS</sub>	-30	_	_	V	I <sub>D</sub> = -1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	-	_	-1	μΑ	V <sub>DS</sub> = -30V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	-1.0	_	-2.5	V	$V_{DS}=-10V$ , $I_{D}=-1mA$
Otatia duain accuracy as atota		_	65	90	mΩ	I <sub>D</sub> = -3.5A, V <sub>G</sub> S= -10V
Static drain-source on-state resistance	R <sub>DS (on)</sub> *	_	100	140	mΩ	I <sub>D</sub> = -1.75A, V <sub>G</sub> s= -4.5V
resistance		_	120	165	mΩ	I <sub>D</sub> = -1.75A, V <sub>G</sub> s= -4V
Forward transfer admittance	Y <sub>fs</sub>   *	1.8	_	_	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1.75A
Input capacitance	Ciss	_	490	_	pF	V <sub>DS</sub> = -10V
Output capacitance	Coss	_	110	_	pF	V <sub>G</sub> S= 0V
Reverse transfer capacitance	Crss	_	75	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	_	10	_	ns	Vpp≒ –15V
Rise time	tr *	_	15	_	ns	ID= -1.75A
Turn-off delay time	t <sub>d (off)</sub> *	_	35	_	ns	Vgs= -10V RL= 8.57Ω
Fall time	t <sub>f</sub> *	-	10	_	ns	R <sub>G</sub> = 10Ω
Total gate charge	Qg *	_	5.5	7.7	nC	V <sub>DD</sub> ≒-15V, V <sub>GS</sub> =-5V
Gate-source charge	Q <sub>gs</sub> *	_	1.5	_	nC	I <sub>D</sub> = -3.5A
Gate-drain charge	Q <sub>gd</sub> *	-	2.0	_	nC	$R_L=4.29\Omega$ , $R_G=10\Omega$

<sup>\*</sup>Pulsed

# $\bullet \textbf{Body diode characteristics} \ (Source-drain) \ (Ta=25^{\circ}C)$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp*	-	_	-1.2	V	I <sub>S</sub> = -1.6A, V <sub>GS</sub> =0V

<sup>\*</sup>Pulsed

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ROHM CO., LTD. 21, Saiin Mizosaki-cho, Ukyo-ku, Kyoto 615-8585, Japan

FAX: +81-75-315-0172

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TEL:+81-75-311-2121

